

 INFORMATION DISCLOSURE CITATION PTO-1449		CUSTOMER NUMBER 26615	ATTORNEY'S DKT No. H1108C	APPLICATION No. 10/830,006			
			APPLICANT(s) Zoran KRIVOKAPIC et al.				
			FILING DATE April 23, 2004	GROUP 2818			
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
TH	2002/0140039	10/3/02	Ballantine et al. Adkisson				
	2002/0130354	9/19/02	Ishii et al. Sekigawa				
	6,475,869	11/5/02	Yu	438	303		
	6,458,662	10/1/02	Yu		286		
	6,300,182	10/9/01	Yu		217		
TH	5,757,038	5/26/98	Wind et al.				
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
TH	EP 1 202 335	5/2/02	Adkisson et al.				
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER TU-TU HO				DATE CONSIDERED 11/02/04			

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).



SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION PTO-1449	CUSTOMER NUMBER 26615	ATTORNEY'S DKT No. H1108C	APPLICATION No. 10/830,006				
		APPLICANT(S) Zoran KRIVOKAPIC et al.					
		FILING DATE April 23, 2004	GROUP Unassigned 2818				
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
TH	6,709,982	03-2004	Buynoski et al.	438	696		
	6,706,571	03-2004	Yu et al.	438	157		
	6,657,252	12-2003	Fried et al.	257	316		
	6,642,090	11-2003	Fried et al.	438	164		
	6,645,797	11-2003	Buynoski et al.	438	157		
	6,657,259	12-2003	Fried et al.	257	350		
TH	6,630,388	10-2003	Sekigawa et al.	438	396		
FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER TH - TH +10				DATE CONSIDERED NOV 2004			

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).

App. 10/830,006

SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION PTO-1449		Customer Number 26615	ATTORNEY'S DKT NO. H1108C		CONTINUATION APPLICATION OF SERIAL NO. 10/348,910	
			APPLICANT(S) Zoran Krivokapic et al.			
			FILING DATE April 23, 2004		GROUP Unassigned 2818	
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
TH	6,583,469 B1	06-24-03	Fried et al.	257	329	01-28-02
TH	US 2004/0048424 A1	03-11-04	Wu et al.	438	154	09-05-02
TH	US 2003/0042531 A1	03-06-03	Lee et al.	257	315	09-04-02
FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes No
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
TH	Digh Hisamoto et al.: "FinFET - A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.					
	Yang-Kyu Choi et al.: "Sub-20nm CMOS Fin FET Technologies," 0-7803-5410-9/99 IEEE, March 2001, 4 pages.					
	Xuejue Huang et al.: "Sub-50 nm P-Channel Fin FET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886.					
	Yang-Kyu Choi et al.: "Nanoscale CMOS Spacer FinFET for the Terabit Era," IEEE Electron Device Letters, Vol. 23, No. 1, January 2002, pages 25-27.					
	Xuejue Huang et al.: "Sub 50-nm FinFET: PMOS," 0-7803-7050-3/01 IEEE, September 1999 4 pages.					
	Co-pending U.S. Application Serial No. 10/614,052 filed July 8, 2003 titled "Narrow Fins By Oxidation In Double-Gate FinFet," 11 page specification, 7 sheets of drawings.					
TH	Co-pending U.S. Application Serial No. 10/699,887 filed November 4, 2003 titled "Self Aligned Damascene Gate," 35 pages.					
EXAMINER TU-TU HO			DATE CONSIDERED Nov 2004			

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).